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Vishay/Siliconix SI2311DS-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com





Si2311DS

Vishay Siliconix

P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
	0.045 at V _{GS} = - 4.5 V	- 3.5		
- 8	0.072 at V _{GS} = - 2.5 V	- 2.8		
	0.120 at V _{GS} = - 1.8 V	- 2.0		

FEATURES

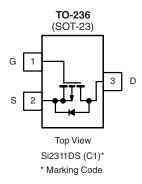
- Halogen-free Option Available
- TrenchFET[®] Power MOSFET



COMPLIANT

APPLICATIONS

Load Switch



Ordering Information: Si2311DS-T1-E3 (Lead (Pb)-free)

Si2311DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unles	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 8		V
Gate-Source Voltage		V _{GS}	± 8		
O	T _A = 25 °C	- I _D	- 3.5	- 3.0	^
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C		- 2.8	- 2.4	
Pulsed Drain Current		I _{DM}	- 10		Α
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 0.8	- 0.6	
Maximum Power Dissipation ^{a, b}	T _A = 25 °C	- P _D	0.96	0.71	W
	T _A = 70 °C		0.62	0.46	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian de Austrian de Austrian de	t ≤ 5 s	- R _{thJA}	100	130	°C/W
Maximum Junction-to-Ambient ^a	Steady State		140	175	
Maximum Junction-to-Foot (Drain)	Steady State		60	75	

Notes

- a. Surface Mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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Datasheet of SI2311DS-T1-E3 - MOSFET P-CH 8V 3A SOT23

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Si2311DS

Vishay Siliconix



SPECIFICATIONS $T_J = 25$			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	_ <u> </u>				<u> </u>		
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V, } I_D = -10 \mu\text{A}$	- 8			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 0.45		- 0.8	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 6.4 V, V _{GS} = 0 V	- 1				
		V _{DS} = - 6.4 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 6			^	
		$V_{DS} \le -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	- 3			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A}$		0.036	0.045	Ω	
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -3 \text{ A}$		0.058	0.072		
		$V_{GS} = -1.8 \text{ V}, I_D = -0.7 \text{ A}$		0.096	0.120	1	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -5 \text{ V}, I_D = -3.5 \text{ A}$		9.0		S	
Diode Forward Voltage	V_{SD}	$I_S = -0.8 \text{ A}, V_{GS} = 0 \text{ V}$			- 1.2	V	
Dynamic ^b				•			
Total Gate Charge	Qg			8.5	12		
Gate-Source Charge	Q _{gs}	$V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_{D} \cong -3.5 \text{ A}$		1.5		nC	
Gate-Drain Charge	Q_{gd}	ID = - 3.3 A		2.1		1	
Input Capacitance	C _{iss}			970			
Output Capacitance	C _{oss}	$V_{DS} = -4 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		485		pF	
Reverse Transfer Capacitance	C _{rss}			160			
Switching ^b				•			
Turn On Time	t _{d(on)}			18	25		
Turn-On Time	t _r	$V_{DD} = -4 \text{ V}, R_L = 4 \Omega$		45	65		
Time Off Time	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V R_G = 6 Ω		40	60	ns	
Turn-Off Time	t _f	G = 0 22		45	65		

- a. For DESIGN AID ONLY, not subject to production testing.
- b. Pulse test: PW \leq 300 μ s, duty cycle \leq 2 %.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

12

10

8

6

4

2

I_D - Drain Current (A)





Si2311DS

125 °C

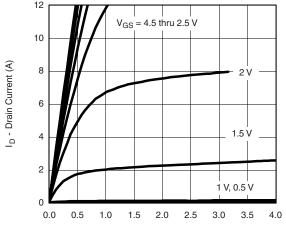
2.5

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T_C = - 55 °

25 °C

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

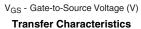


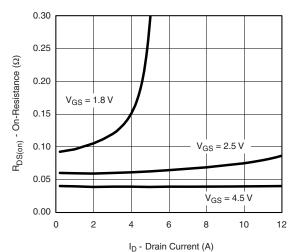
V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics

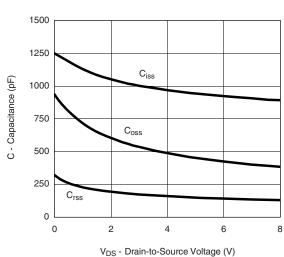


0.0 0.5 1.0 1.5 2.0



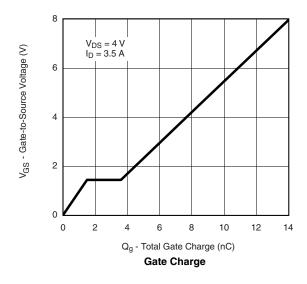


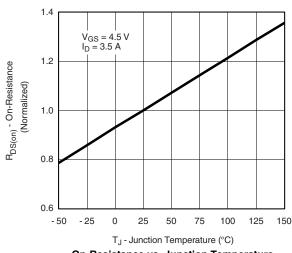
On-Resistance vs. Drain Current



Dialii-lo-Source vollage (v

Capacitance





On-Resistance vs. Junction Temperature

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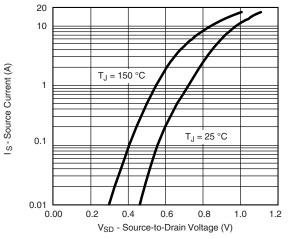


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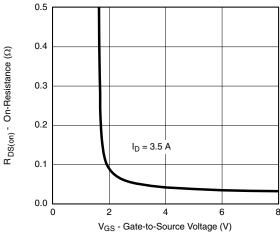
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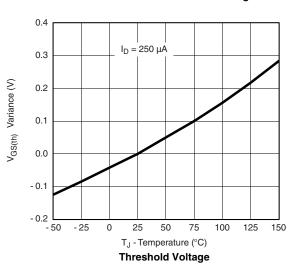
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

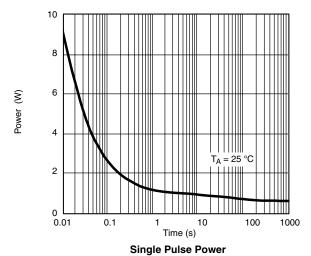


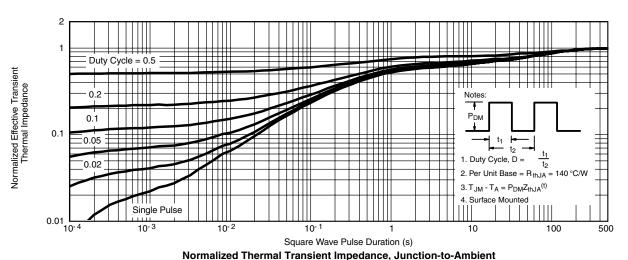
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage







Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71813.



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Datasheet of SI2311DS-T1-E3 - MOSFET P-CH 8V 3A SOT23

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